

Description

The H11G1 H11G2 H11G3 series combine an AlGaAs infrared emitting diode as the emitter which is optically coupled to a silicon planar darlington phototransistor detector in a plastic DIP6 package with different lead forming options

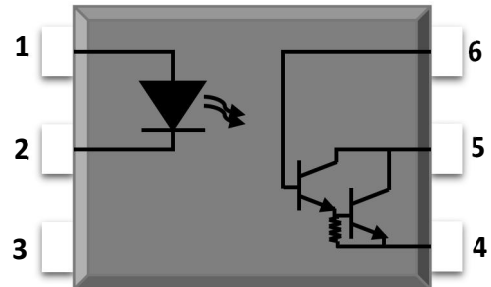
Features

- High isolation 5000 VRMS
- DC input with transistor output
- Operating temperature range - 55 °C to 110 °C
- RoHS & REACH Compliance
- MSL class 1
- Regulatory Approvals
 - UL - UL1577
 - VDE - EN60747-5-5(VDE0884-5)
 - CQC - GB4943.1, GB8898
 - cUL- CSA Component Acceptance Service Notice No. 5A

Applications

- Low power logic circuits
- Telecommunications equipment
- Portable electronics
- Interfacing coupling systems of different potentials and impedances

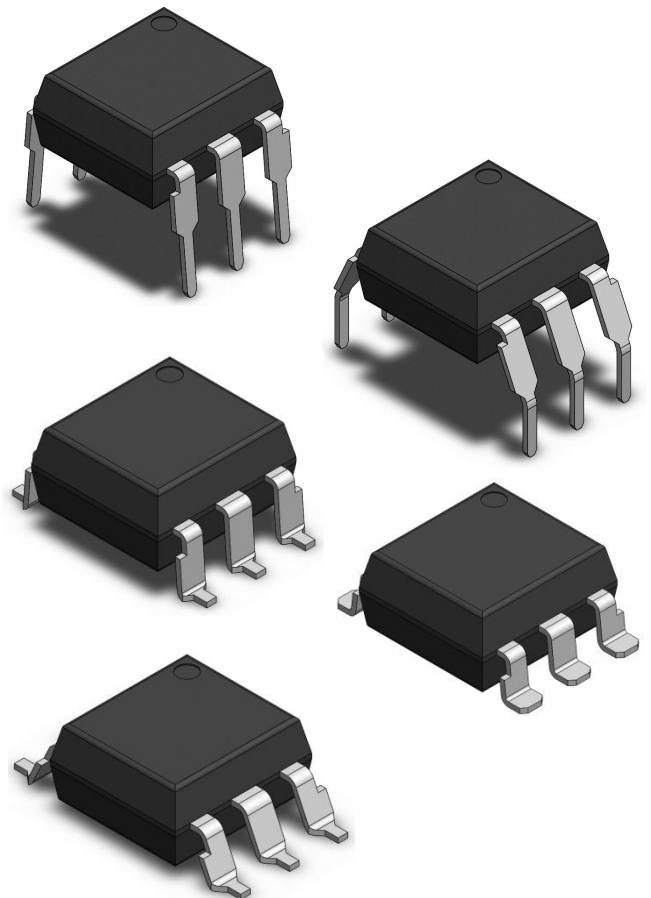
SCHEMATIC



PIN DEFINITION

1. Anode	6. Base
2. Cathode	5. Collector
3. NC	4. Emitter

PACKAGE OUTLINE





H11G1 H11G2 H11G3

LIGHTNING DIP6, DC Input, High Voltage Photo Darlington Transistor Couple

ABSOLUTE MAXIMUM RATINGS					
PARAMETER	SYMBOL	VALUE	UNIT	NOTE	
INPUT					
Forward Current	I_F	60	mA		
Peak Forward Current($t=10\mu s$)	I_{FM}	1	A	1	
Reverse Voltage	V_R	6	V		
Power Dissipation($T_A=25^\circ C$)	P_D	120	mW		
OUTPUT					
Collector - Emitter Voltage	V_{CEO}	H11G1	100	V	
		H11G2	80		
		H11G3	55		
Collector-Base Breakdown Voltage	V_{CBO}	H11G1	100	V	
		H11G2	80		
		H11G3	55		
Emitter-Base Breakdown Voltage	V_{EBO}	7	V		
Collector Current	I_C	150	mA		
Power Dissipation($T_A=25^\circ C$)	P_C	150	mW		
COMMON					
Total Power Dissipation	P_{tot}	200	mW		
Isolation Voltage	V_{iso}	5000	V _{rms}	2	
Operating Temperature	T_{opr}	-55~+110	$^\circ C$		
Storage Temperature	T_{stg}	-55~+125	$^\circ C$		
Soldering Temperature	T_{sol}	260	$^\circ C$		

Note 1. AC For 1 Minute, R.H. = 40 ~ 60%

Note 2. For 10 seconds



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ELECTRICAL OPTICAL CHARACTERISTICS at Ta=25°C							
PARAMETER	SYMBOL	MIN	TYP.	MAX	UNIT	TEST CONDITION	NOTE
INPUT							
Forward Voltage	VF	-	1.24	1.4	V	IF=10mA	
Reverse Current	IR	-	-	10	μA	VR=6V	
Input Capacitance	Cin	-	50	-	pF	V=0, f=1kHz	
OUTPUT							
Collector Dark Current	ICEO	-	-	100	nA	VCE=80V	H11G1
						VCE=60V	H11G2
						VCE=30V	H11G3
Collector-Emitter Breakdown Voltage	BVCEO	H11G1	100	-	-	V	IC=0.1mA
		H11G2	80				
		H11G3	55				
Collector-Base Breakdown Voltage	BVCBO	H11G1	100	-	-	V	IC=0.1mA
		H11G2	80				
		H11G3	55				
Emitter-Collector Breakdown Voltage	BEBO	7	-	-	V	IE=0.1mA	



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TRANSFER CHARACTERISTICS							
Current Transfer Ratio	CTR	H11G1/2	500	-	-	%	IF=1mA, VCE=5V
		H11G3	200	-	-		
		H11G1/2	500	-	-		IF=10mA, VCE=1V
Collector-Emitter Saturation Voltage	V _{CE(sat)}	H11G1/2	-	0.85	1	V	IF=16mA, IC=50mA
		H11G1/2	-	0.75	1		IF=1mA, IC=1mA
		H11G3	-	0.85	1.2		IF=20mA, IC=50mA
Isolation Resistance	R _{io}		10 ¹¹	-	-	Ω	V _{io} =500Vdc.
Floating Capacitance	C _{io}		-	0.8	-	pF	V=0, f=1MHz
Response Time (Rise)	tr	H11G1	-	60	300	μs	VCE=2V, IC=10mA RL=100Ω
Response Time (Fall)	tf	H11G1	-	53	250	μs	



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CHARACTERISTIC CURVES

Fig.1 Forward Current vs. Ambient Temperature

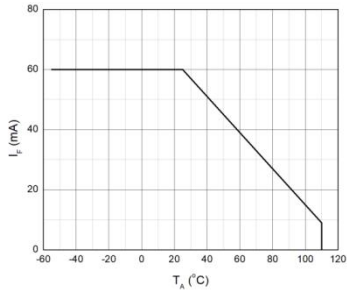


Fig.2 Collector Power Dissipation vs. Ambient Temperature

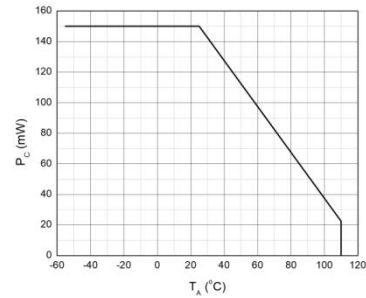


Fig.3 Forward Current vs. Forward Voltage

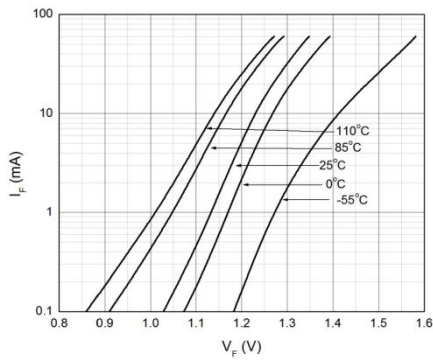


Fig.4 Collector Dark Current vs. Ambient Temperature

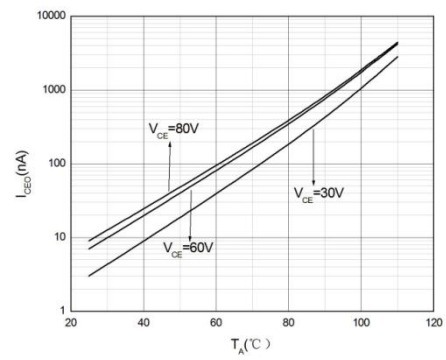


Fig.5 Collector Current vs. Collector-emitter Voltage

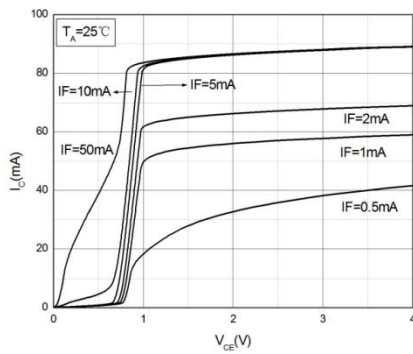
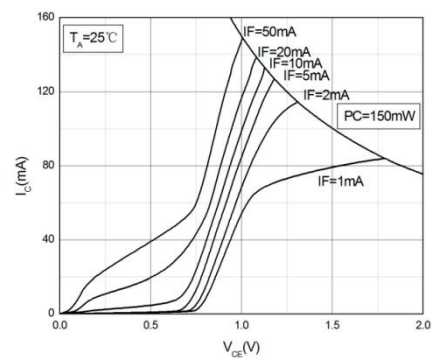


Fig.6 Collector Current vs. Collector-emitter Voltage





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CHARACTERISTIC CURVES

Fig.7 Normalized Current Transfer Ratio vs. Forward Current

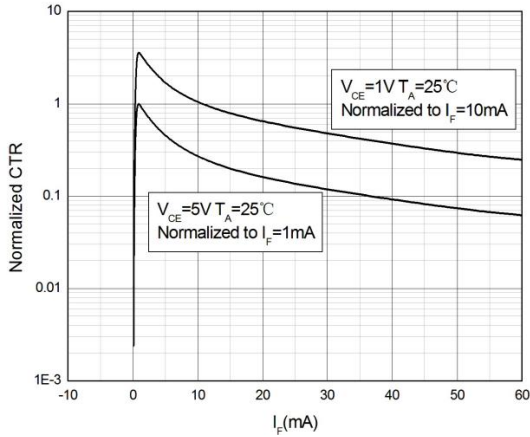


Fig.8 Normalized Current Transfer Ratio vs. Ambient Temperature

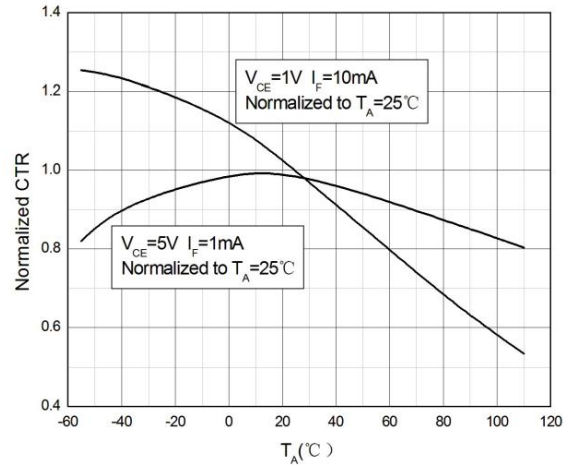


Fig.9 Collector-emitter Saturation Voltage vs. Ambient Temperature

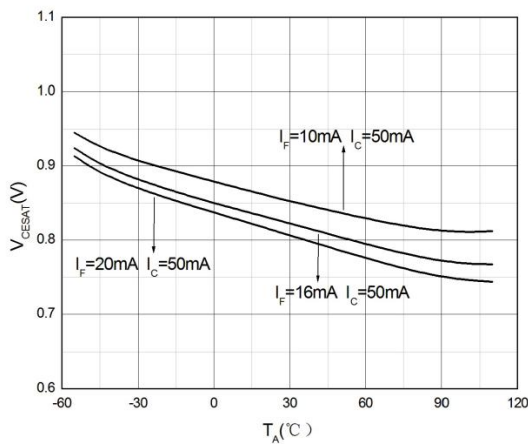
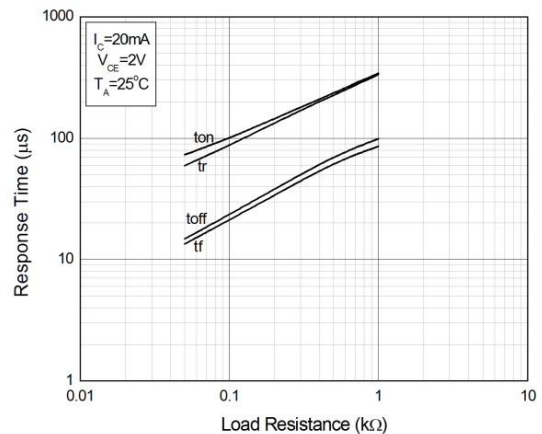


Fig.10 Switching Time vs. Load Resistance



TEST CIRCUITS

Fig.11 Test Circuits of Response Time

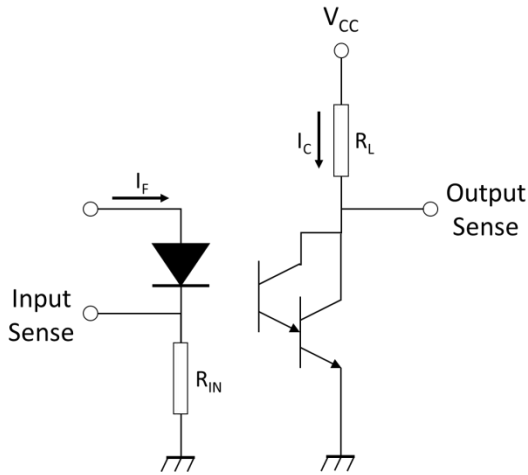


Fig.12 Curves of Response Time

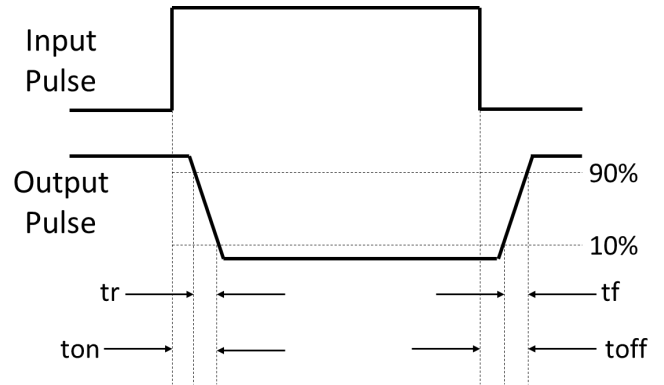
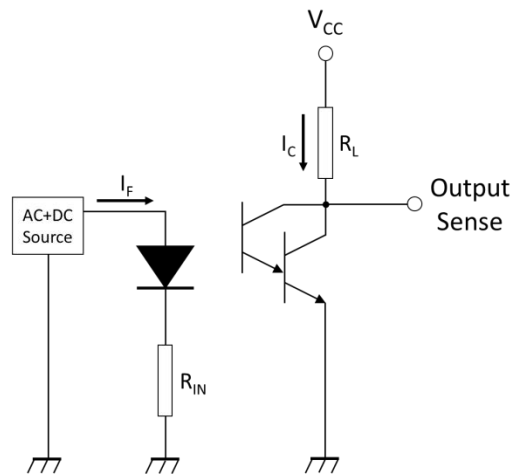
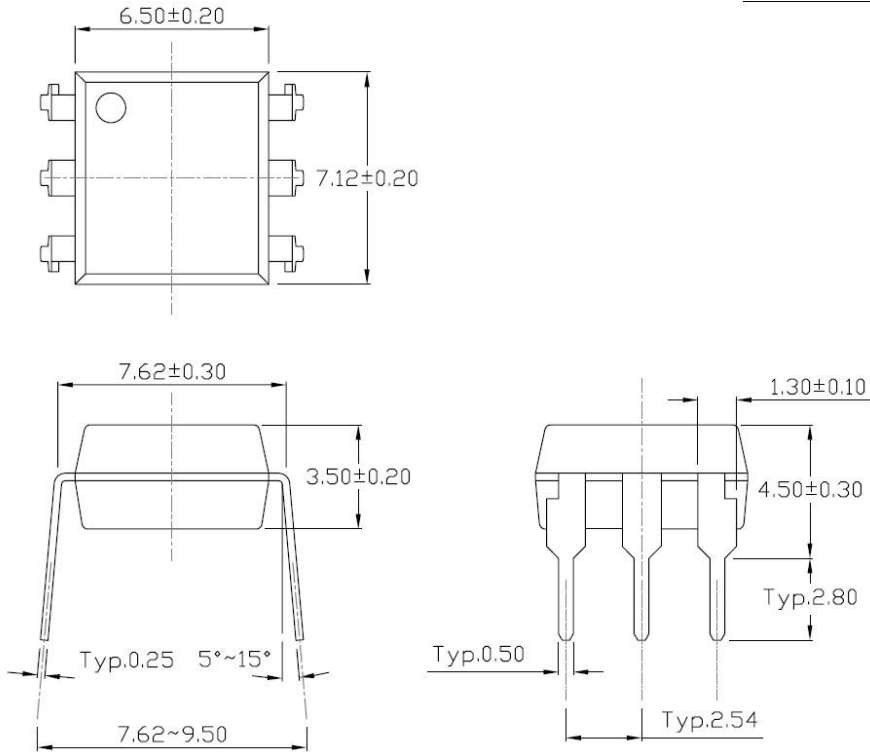


Fig.13 Test Circuits of Frequency Response

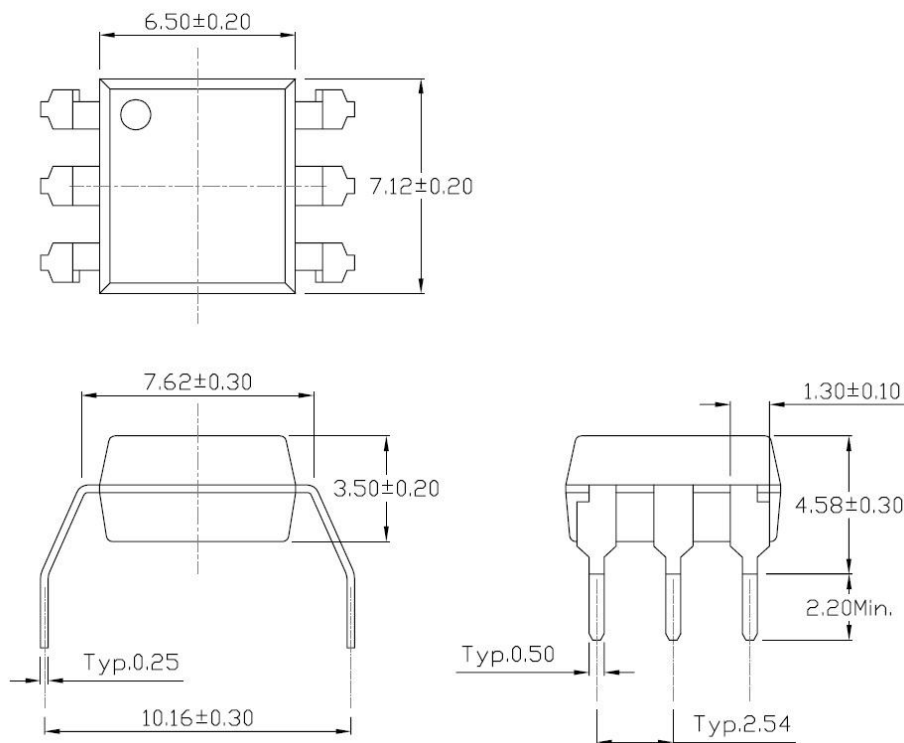


PACKAGE DIMENSIONS (Dimensions in mm unless otherwise stated)

Standard DIP – Through Hole (DIP Type)

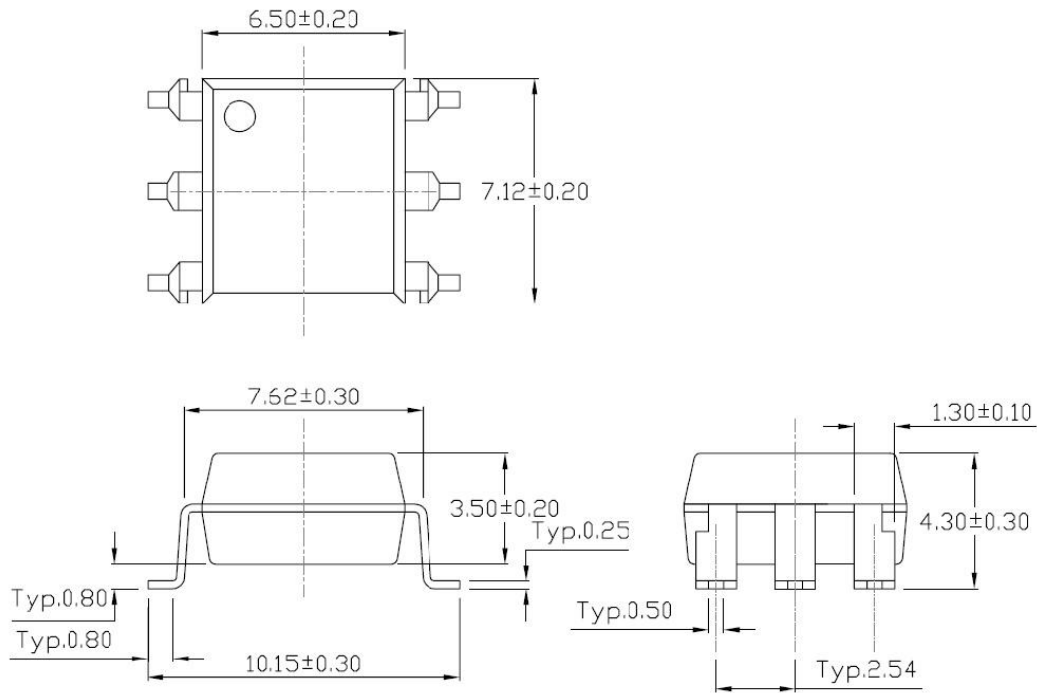


Gullwing (400mil) Lead Forming – Through Hole (M Type)

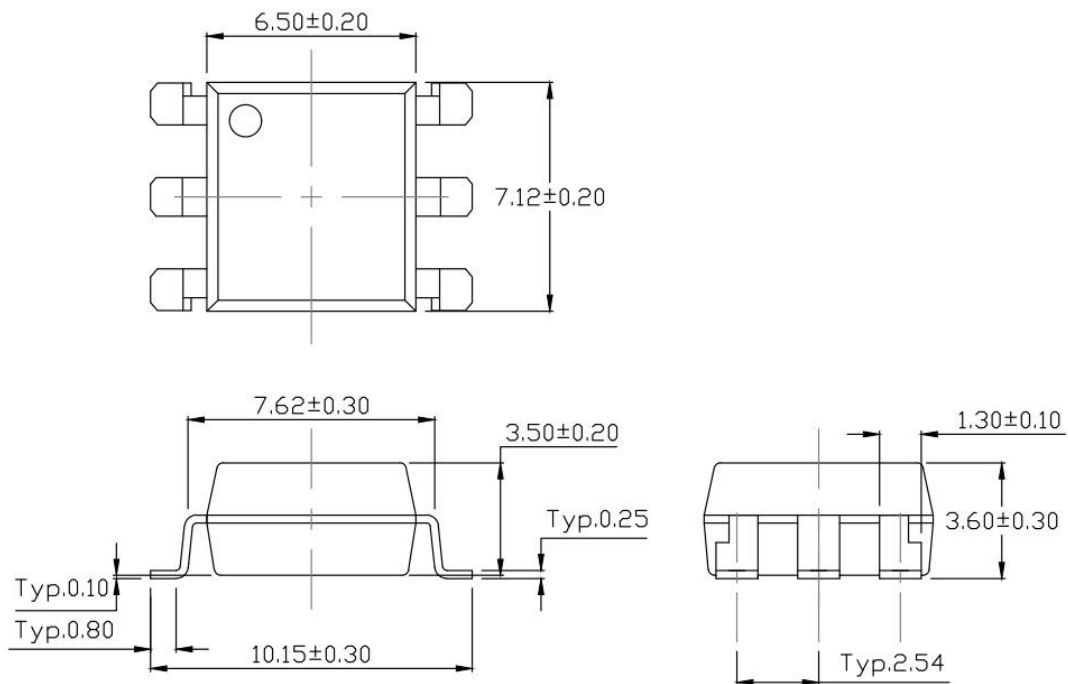


PACKAGE DIMENSIONS (Dimensions in mm unless otherwise stated)

Surface Mount Lead Forming (S Type)

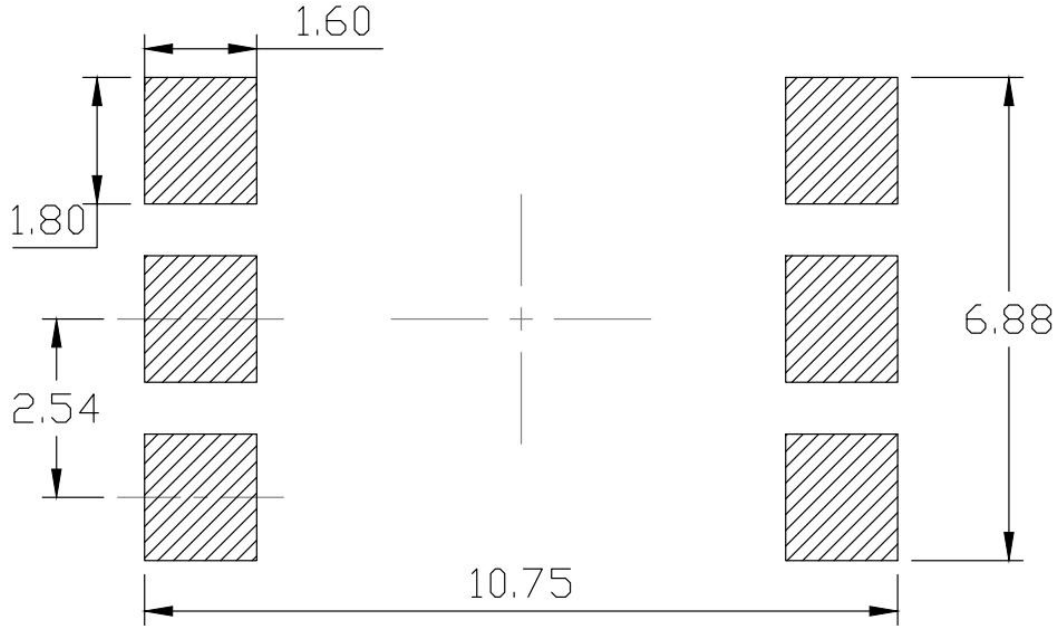


Surface Mount (Low Profile) Lead Forming (SL Type)

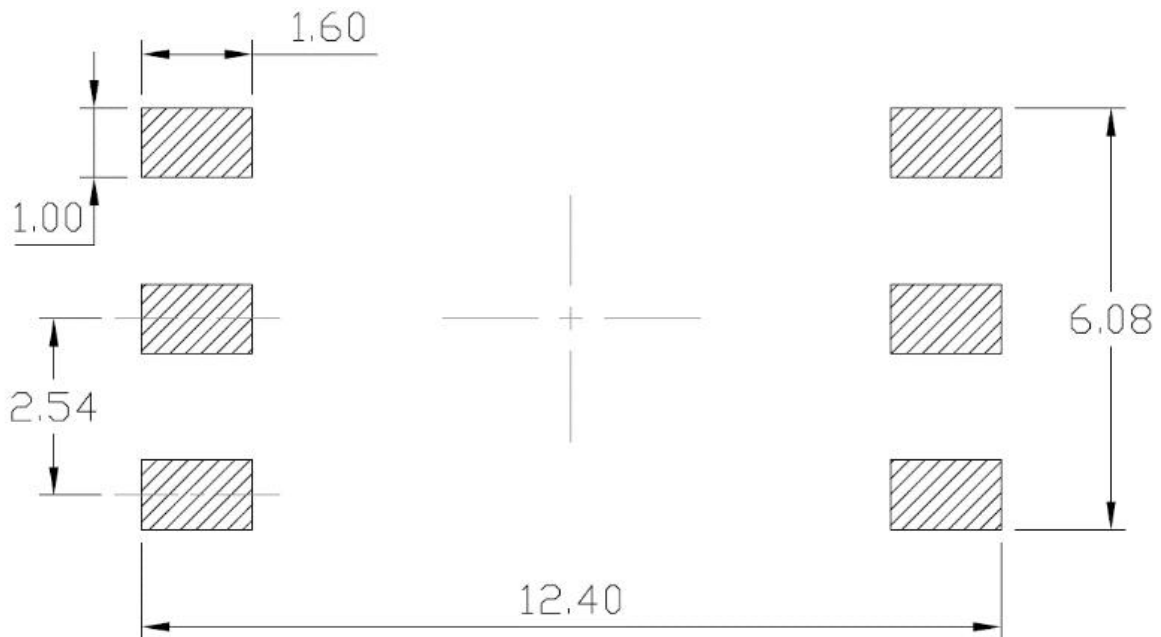


Recommended Solder Mask (Dimensions in mm unless otherwise stated)

Surface Mount Lead Forming & Surface Mount (Low Profile) Lead Forming



Surface Mount (Gullwing) Lead Forming



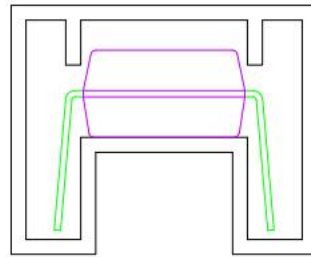
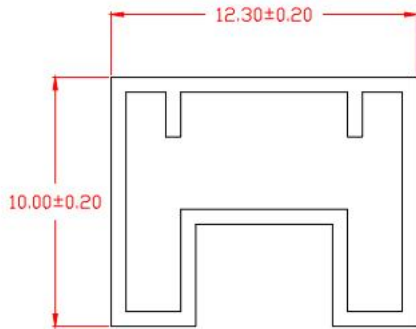


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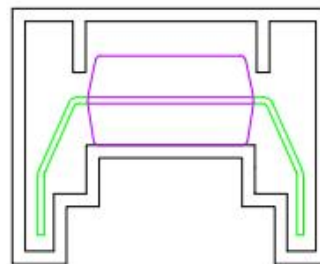
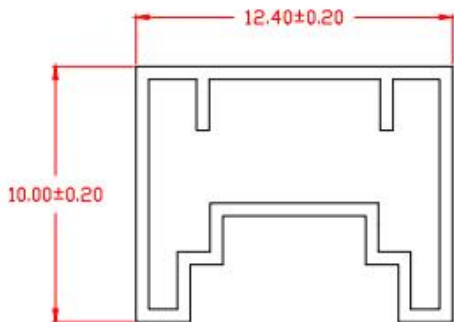
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TUBE SPECIFICATIONS (Dimensions in mm unless otherwise stated)

Standard DIP



Option M



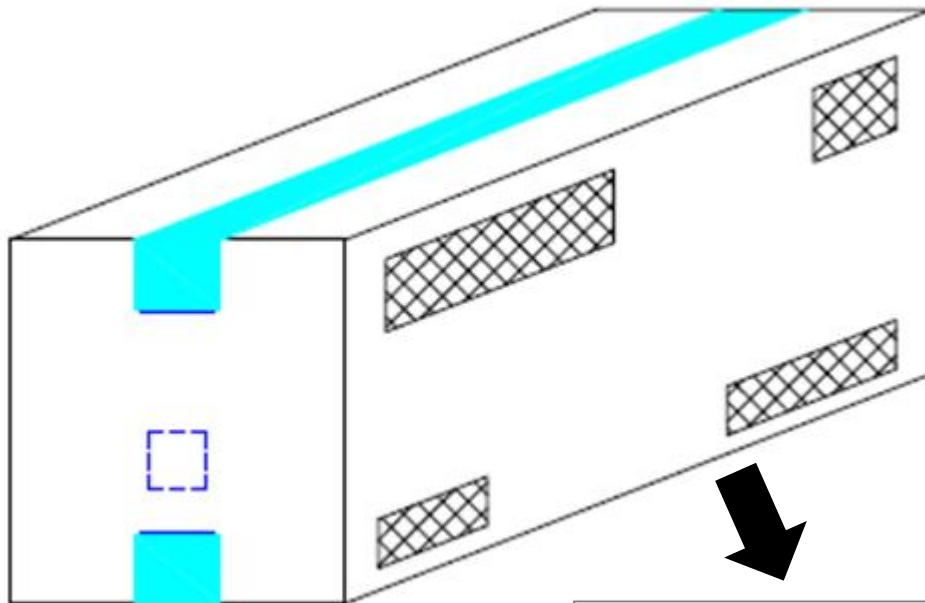
BOX SPECIFICATIONS (Tube Type)

Inner Box

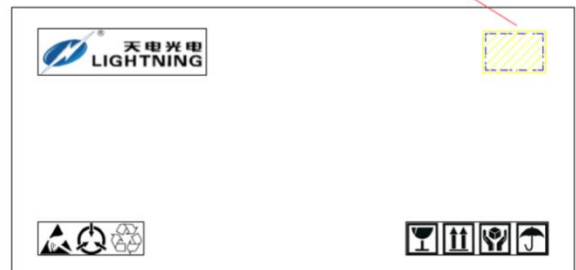


- L x W x H = 52.5cm x 10.7cm x 4.7cm

Outer Box

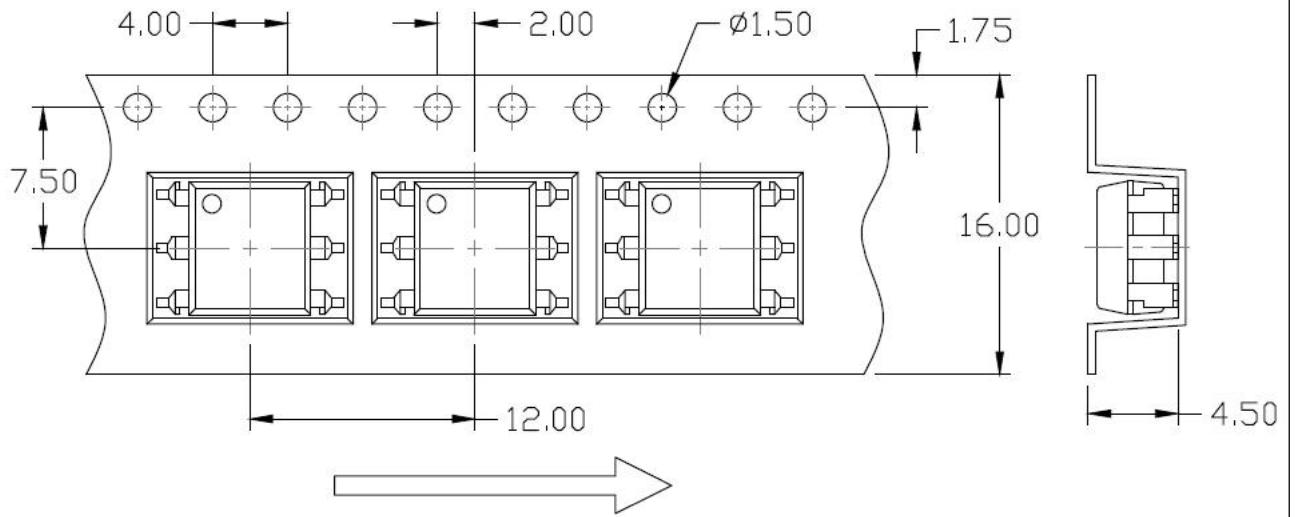


- L x W x H = 53.5cm x 23.5cm x 25.5cm

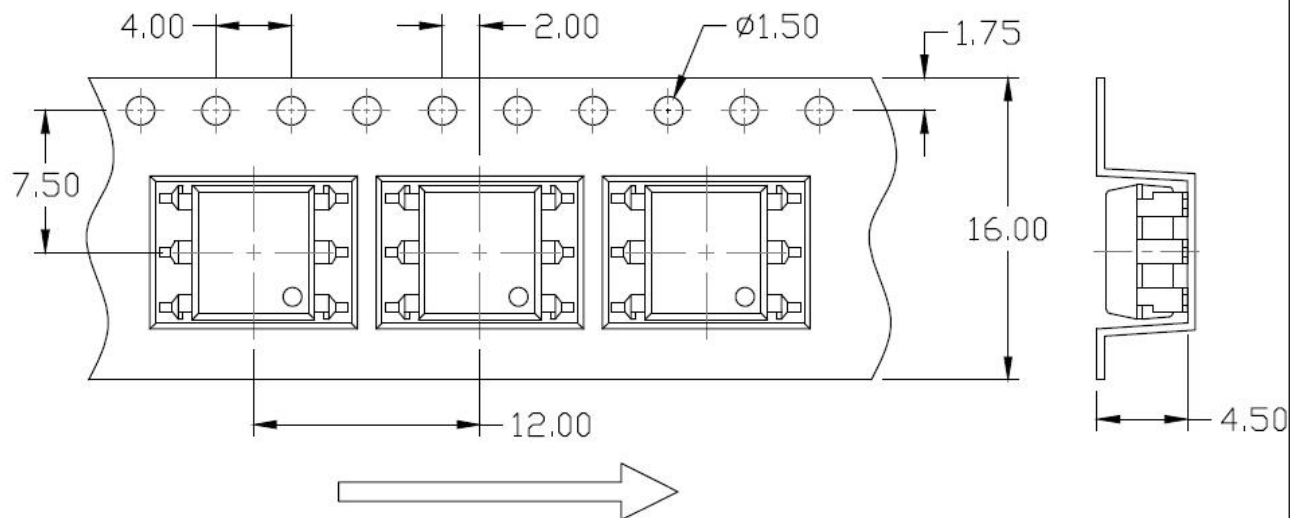


Carrier Tape Specifications (Dimensions in mm unless otherwise stated)

Option S(T1)

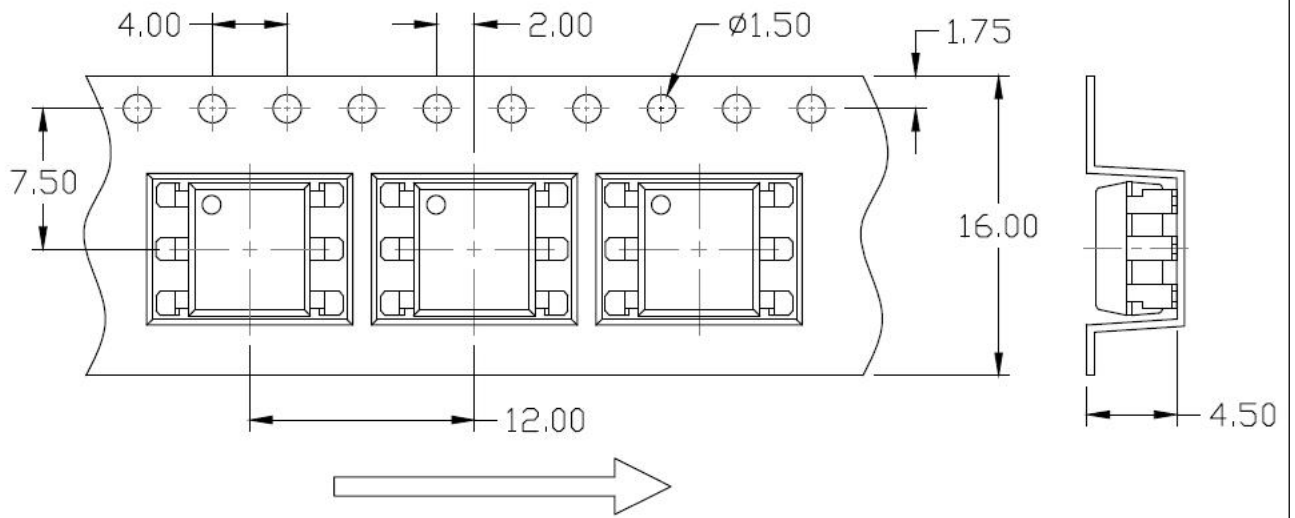


Option S(T2)

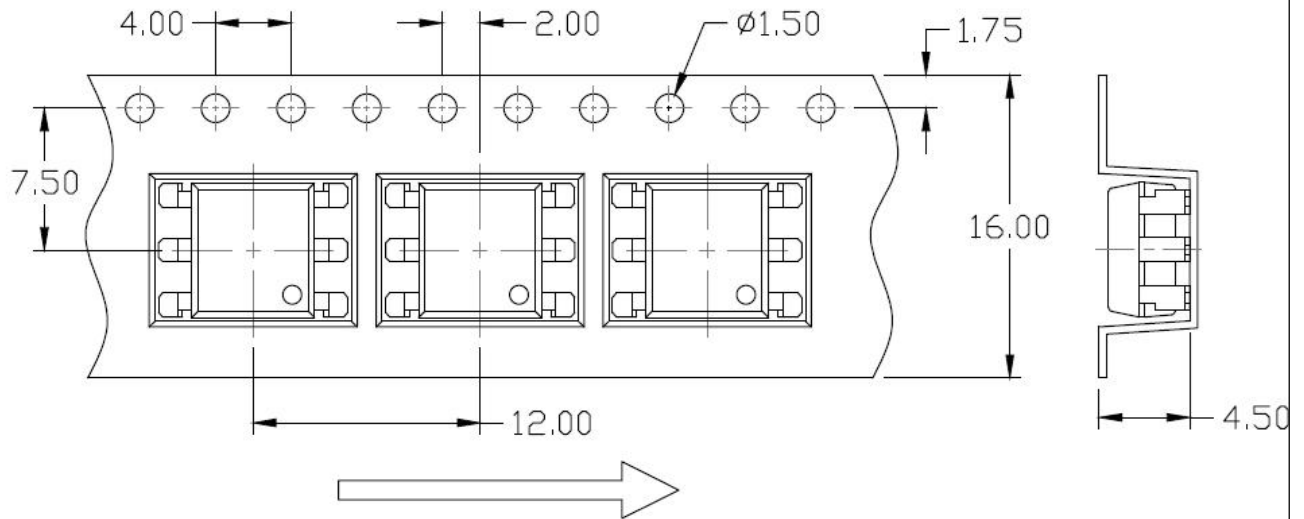


Carrier Tape Specifications (Dimensions in mm unless otherwise stated)

Option SL(T1)



Option SL(T2)



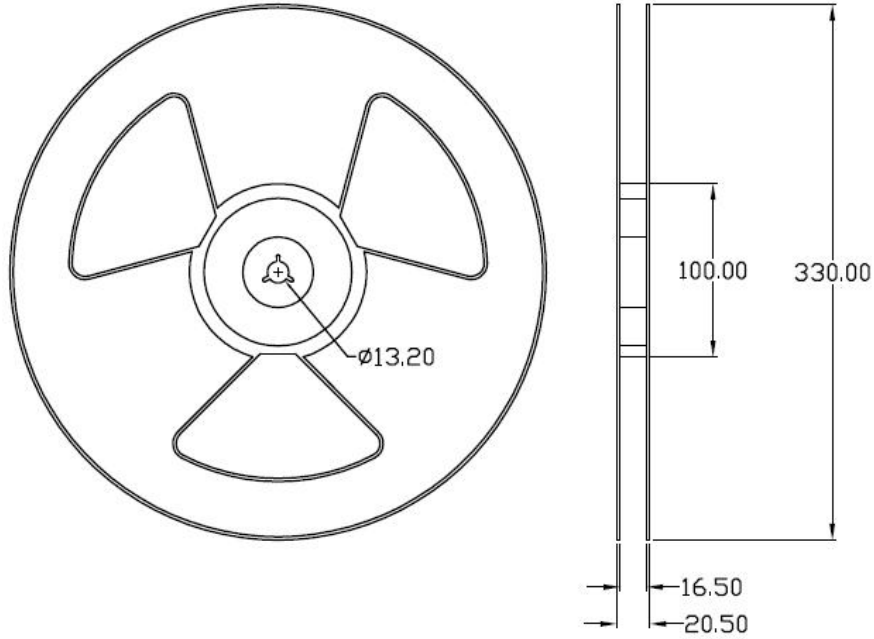


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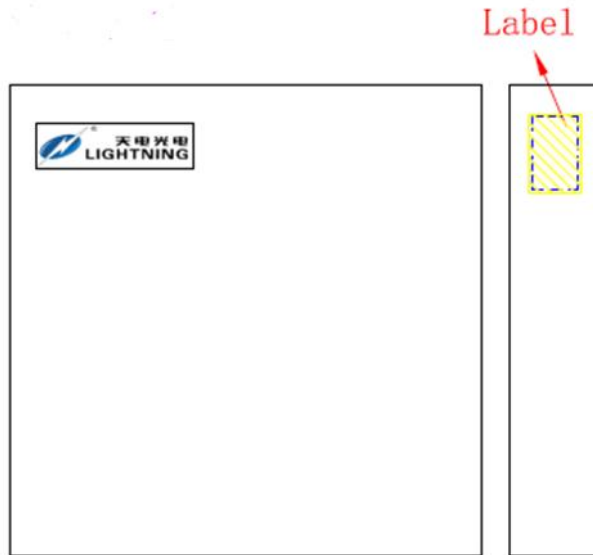
REEL SPECIFICATIONS (Dimensions in mm unless otherwise stated)

Option S & Option SL



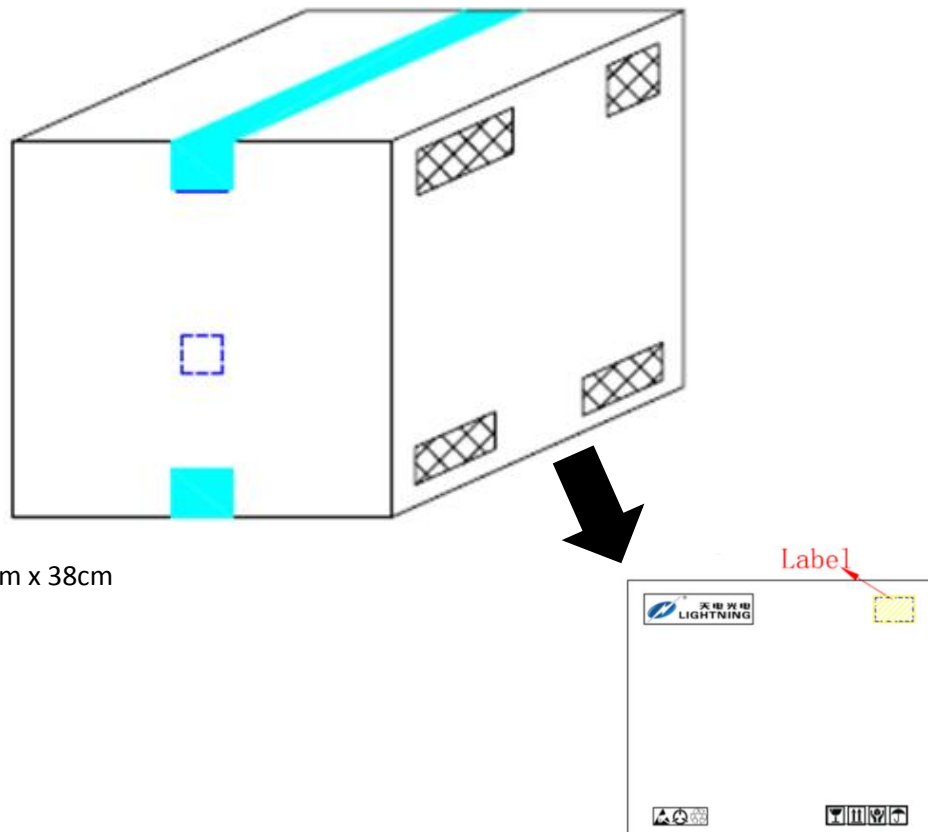
BOX SPECIFICATIONS (Reel Type)

Inner Box



- L x W x H = 36cm x 36cm x 6.9cm

Outer Box



- L x W x H = 45cm x 38cm x 38cm

ORDERING AND MARKING INFORMATION

MARKING INFORMATION



TD : Company Abbr.
H11GX : Part Number & Rank
V : VDE Option
Y : Fiscal Year
A : Manufacturing Code
WW : Work Week

ORDERING INFORMATION

H11GX(Y)(Z)-GV

H11GX – Part Number and Rank
Y – Lead Form Option
 (M/S/SL/None)
Z – Tape and Reel Option (T1/T2)
G – Material Option
 (G: Green, None: Non-Green)
V – VDE Option (V or None)

LABEL INFORMATION



PACKING QUANTITY

Option	Quantity	Quantity – Inner box	Quantity – Outer box
None	65 Units/Tube	32 Tubes/Inner box	10 Inner box/Outer box = 20.8k Units
M	65 Units/Tube	32 Tubes/Inner box	10 Inner box/Outer box = 20.8k Units
S(T1)	1000 Units/Reel	3 Reels/Inner box	5 Inner box/Outer box = 15k Units
S(T2)	1000 Units/Reel	3 Reels/Inner box	5 Inner box/Outer box = 15k Units
SL(T1)	1000 Units/Reel	3 Reels/Inner box	5 Inner box/Outer box = 15k Units
SL(T2)	1000 Units/Reel	3 Reels/Inner box	5 Inner box/Outer box = 15k Units

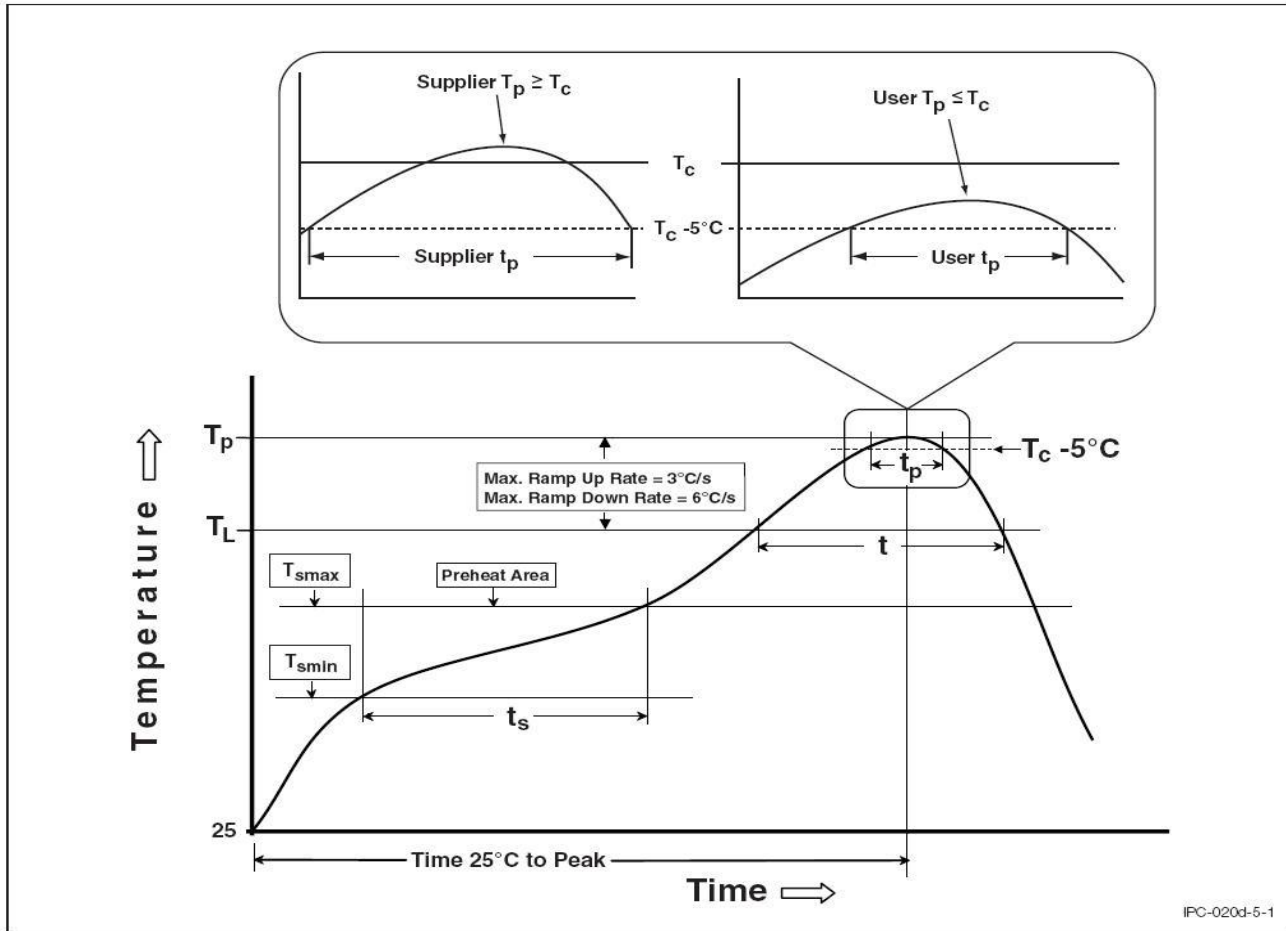


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REFLOW INFORMATION

REFLOW PROFILE



Profile Feature	Sn-Pb Assembly Profile	Pb-Free Assembly Profile
Temperature Min. (T _{smin})	100	150°C
Temperature Max. (T _{smax})	150	200°C
Time (t _s) from (T _{smin} to T _{smax})	60-120 seconds	60-120 seconds
Ramp-up Rate (t _L to t _P)	3°C/second max.	3°C/second max.
Liquidous Temperature (T _L)	183°C	217°C
Time (t _L) Maintained Above (T _L)	60 – 150 seconds	60 – 150 seconds
Peak Body Package Temperature	235°C +0°C / -5°C	260°C +0°C / -5°C
Time (t _P) within 5°C of 260°C	20 seconds	30 seconds
Ramp-down Rate (T _P to T _L)	6°C/second max	6°C/second max
Time 25°C to Peak Temperature	6 minutes max.	8 minutes max.

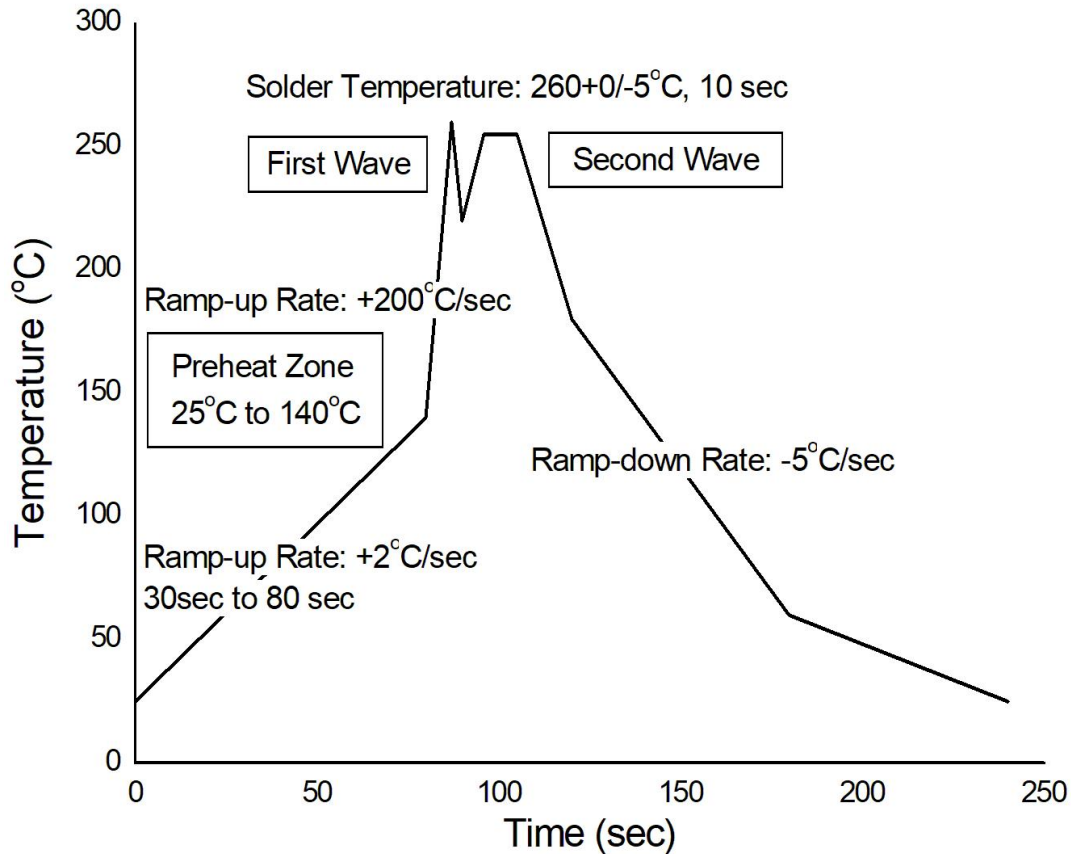


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DIP6, DC Input, High Voltage Photo Darlington Transistor Couple

TEMPERATURE PROFILE OF SOLDERING

WAVE SOLDERING (JESD22-A111 COMPLIANT)



HAND SOLDERING BY SOLDERING IRON

Soldering Temperature	$380 \pm 0 / -5^{\circ}\text{C}$
Soldering Time	3 sec max.

- One time soldering is recommended for all soldering method.
- Do not solder more than three times for IR reflow soldering.



LIGHTNING

H11G1 H11G2 H11G3

DIP6, DC Input, High Voltage Photo Darlington Transistor Couple

DISCLAIMER

- LIGHTNING is continually improving the quality, reliability, function and design. LIGHTNING reserves the right to make changes without further notices.
- The characteristic curves shown in this datasheet are representing typical performance which are not guaranteed.
- LIGHTNING makes no warranty, representation or guarantee regarding the suitability of the products for any particular purpose or the continuing production of any product. To the maximum extent permitted by applicable law, LIGHTNING disclaims (a) any and all liability arising out of the application or use of any product, (b) any and all liability, including without limitation special, consequential or incidental damages, and (c) any and all implied warranties, including warranties of fitness for particular
- The products shown in this publication are designed for the general use in electronic applications such as office automation, equipment, communications devices, audio/visual equipment, electrical application and instrumentation purpose, non-infringement and merchantability.
- This product is not intended to be used for military, aircraft, automotive, medical, life sustaining or lifesaving applications or any other application which can result in human injury or death.
- Please contact LIGHTNING sales agent for special application request.
- Immerge unit's body in solder paste is not recommended.
- Parameters provided in datasheets may vary in different applications and performance may vary over time. All operating parameters, including typical parameters, must be validated in each customer application by the customer's technical experts. Product specifications do not expand or otherwise modify LIGHTNING's terms and conditions of purchase, including but not limited to the warranty expressed therein.
- Discoloration might be occurred on the package surface after soldering, reflow or long-time use. It neither impacts the performance nor reliability.